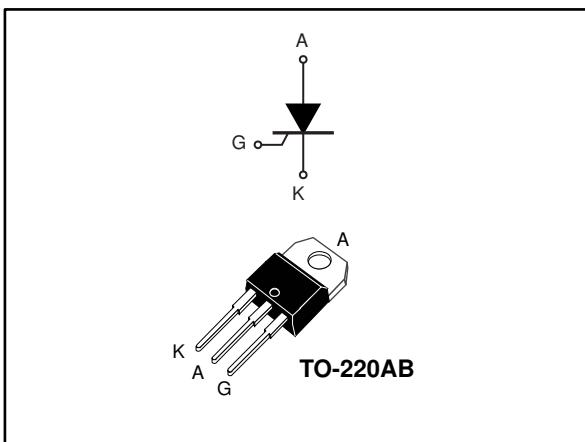


## High temperature 16 A SCRs

Datasheet - production data



### Features

- High junction temperature:  $T_j = 150^\circ\text{C}$
- Gate triggering current  $I_{GT} = 6 \text{ mA}$
- High noise immunity  $dV/dt = 200 \text{ V}/\mu\text{s}$  up to  $150^\circ\text{C}$
- Blocking voltage  $V_{DRM}/V_{RRM} = 600 \text{ V}$
- High turn-on current rise  $di/dt: 100 \text{ A}/\mu\text{s}$
- ECOPACK®2 compliant component

### Applications

- Motorbikes voltage regulator circuits
- Inrush current limiting circuits
- Motor control circuits and starters
- Light dimmers
- Solid state relays

### Description

Designed with high immunity switching to external surges, the device offers robust switching up to its  $150^\circ\text{C}$  maximum  $T_j$ .

The combination of noise immunity and low gate triggering current allows to design strong and compact control circuit.

**Table 1: Device summary**

Order code	Package	$V_{DRM}/V_{RRM}$	$I_{GT}$
TN1605H-6T	TO-220AB	600	6 mA

# 1 Characteristics

Table 2: Absolute maximum ratings (limiting values,  $T_j = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter			Value	Unit
$I_{T(\text{RMS})}$	RMS on-state current (180° conduction angle)		$T_c = 133^\circ\text{C}$	16	A
$I_{T(\text{AV})}$	Average on-state current (180° conduction angle)		$T_c = 133^\circ\text{C}$	10	A
			$T_c = 138^\circ\text{C}$	8	
			$T_c = 142^\circ\text{C}$	6	
$I_{TSM}$	Non repetitive surge peak on-state current	$t_p = 8.3\text{ ms}$	$T_j$ initial = 25 °C	153	A
		$t_p = 10\text{ ms}$		140	
$I^2t$	$I^2t$ value for fusing	$t_p = 10\text{ ms}$		98	$\text{A}^2\text{s}$
$dI/dt$	Critical rate of rise of on-state current	$I_G = 2 \times I_{GT}, t_r \leq 100\text{ ns},$	$f = 60\text{ Hz}$	100	$\text{A}/\mu\text{s}$
$V_{DRM}/V_{RRM}$	Repetitive peak off-state voltage		$T_j = 150^\circ\text{C}$	600	V
$V_{DSM}/V_{RSM}$	Non repetitive surge peak off-state voltage	$t_p = 10\text{ ms}$		700	V
$P_{G(\text{AV})}$	Average gate power dissipation		$T_j = 150^\circ\text{C}$	1	W
$V_{RGM}$	Maximum peak reverse gate voltage			5	V
$I_{GM}$	Peak gate current	$t_p = 20\text{ }\mu\text{s}$	$T_j = 150^\circ\text{C}$	4	A
$P_{GM}$	Peak gate power dissipation	$t_p = 20\text{ }\mu\text{s}$	$T_j = 150^\circ\text{C}$	40	W
$P_{G(\text{AV})}$	Average gate power dissipation		$T_j = 150^\circ\text{C}$	1	W
$T_{stg}$	Storage junction temperature range			-40 to +150	°C
$T_j$	Operating junction temperature range			-40 to +150	°C
$T_L$	Maximum lead temperature for soldering during 10 s			260	°C

Table 3: Dynamic characteristics

Symbol	Parameter	$T_j$		Value	Unit
$I_{GT}$	$V_D = 12\text{ V}, R_L = 33\text{ }\Omega$	25 °C	Min.	3.5	mA
			Typ.	4.5	
			Max.	6	
$V_{GT}$			Max.	1.3	V
$V_{GD}$	$V_D = 600\text{ V}, R_L = 3.3\text{ k}\Omega$	150 °C	Min.	0.15	V
$I_L$	$I_G = 1.2 \times I_{GT}$	25 °C	Max.	40	mA
$I_H$	$I_T = 500\text{ mA, gate open}$		Max.	20	
$dV/dt$	$V_D = 402\text{ V, gate open}$	150 °C	Min.	200	$\text{V}/\mu\text{s}$
$t_{gt}$	$I_{TM} = 32\text{ A, }V_D = 402\text{ V, }I_G = 12\text{ mA, } (dI_G/dt) \text{ max} = 0.2\text{ A}/\mu\text{s}$	25 °C	Typ.	1.9	μs
$t_q$	$I_{TM} = 32\text{ A, }V_D = 402\text{ V, } (dI/dt)_{off} = 30\text{ A}/\mu\text{s, } V_R = 25\text{ V, } dV_D/dt = 20\text{ V}/\mu\text{s}$	150 °C	Typ.	70	μs

**Table 4: Static electrical characteristics**

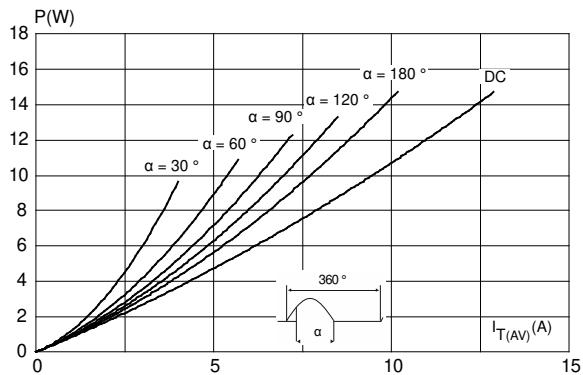
<b>Symbol</b>	<b>Test Conditions</b>	<b>T<sub>j</sub></b>		<b>Value</b>	<b>Unit</b>
V <sub>TM</sub>	I <sub>TM</sub> = 32 A, t <sub>p</sub> = 380 µs	25 °C	Max.	1.6	V
V <sub>TO</sub>	Threshold on-state voltage	150 °C	Max.	0.82	V
R <sub>D</sub>	Dynamic resistance	150 °C	Max.	25	mΩ
I <sub>DRM</sub> /I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub>	25 °C	Max.	5	µA
		125 °C		1.5	mA
		150 °C		3.1	

**Table 5: Thermal resistance**

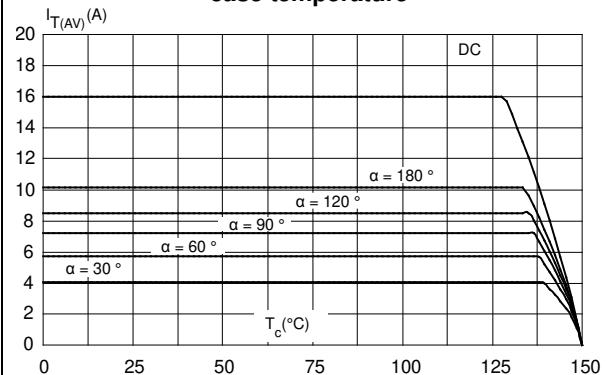
<b>Symbol</b>	<b>Parameter</b>	<b>Value</b>	<b>Unit</b>
R <sub>th(j-c)</sub>	Junction to case (DC)	1.1	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (DC)	60	

## 1.1 Characteristics (curves)

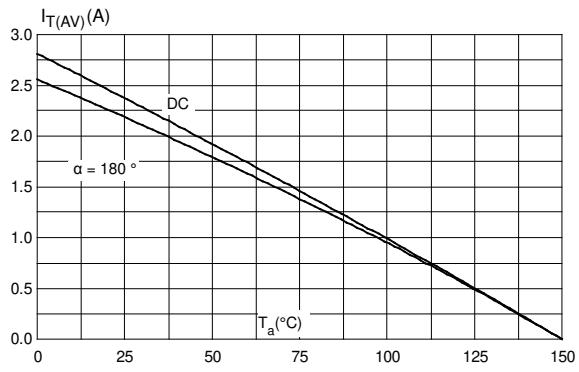
**Figure 1: Maximum average power dissipation versus average on-state current**



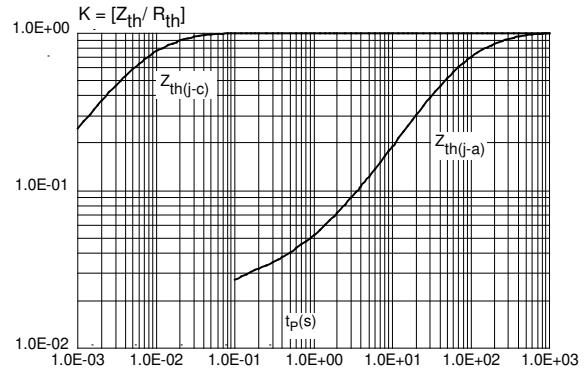
**Figure 2: Average and DC on-state current versus case temperature**



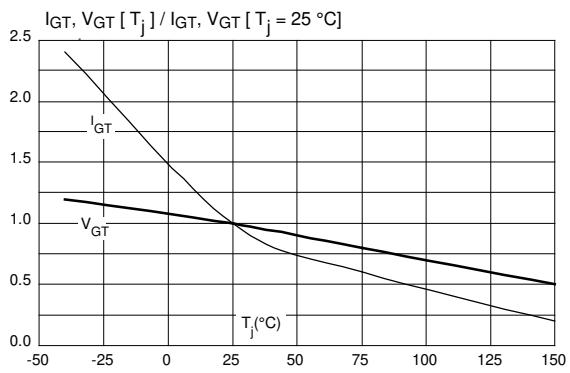
**Figure 3: Average and DC on-state current versus ambient temperature**



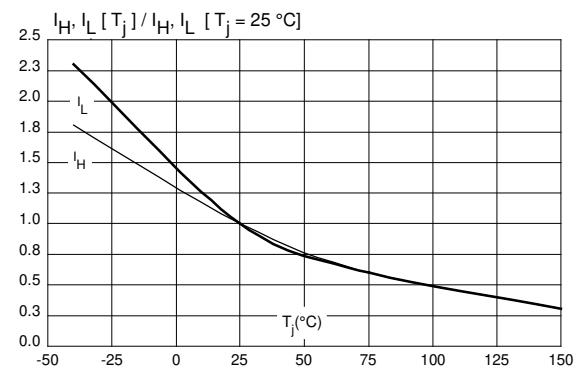
**Figure 4: Relative variation of thermal impedance versus pulse duration**



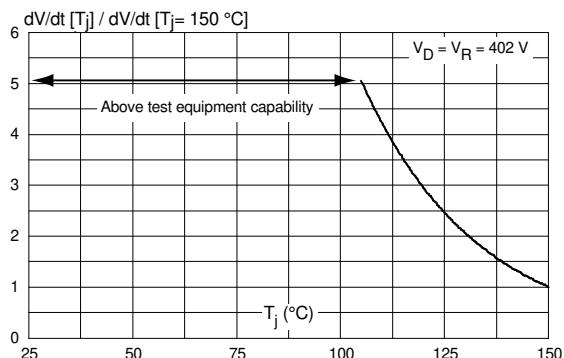
**Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)**



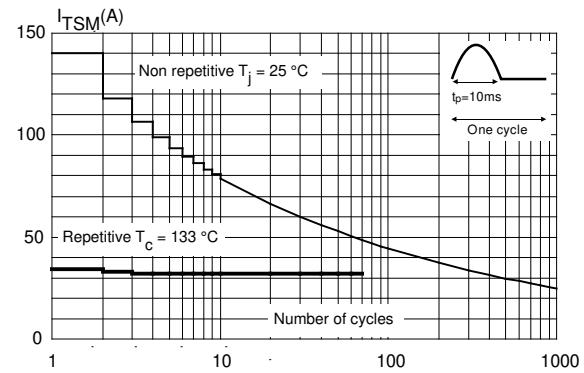
**Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)**



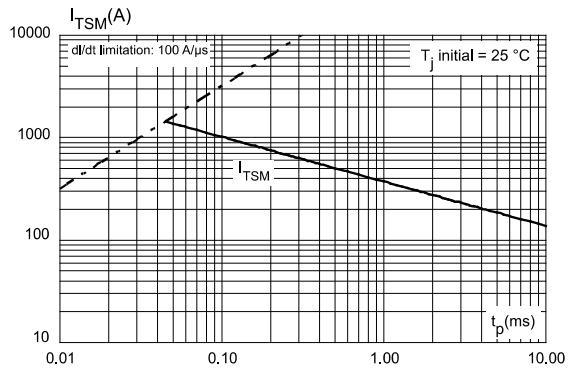
**Figure 7: Relative variation of static dV/dt immunity versus junction temperature (typical values)**



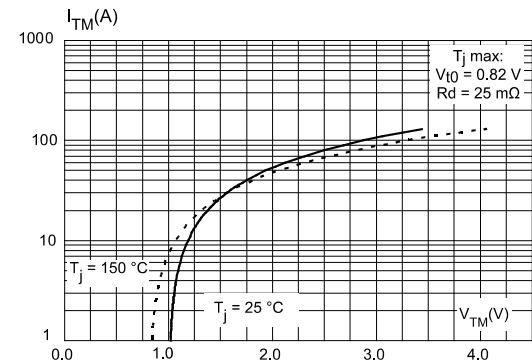
**Figure 8: Surge peak on-state current versus number of cycles**



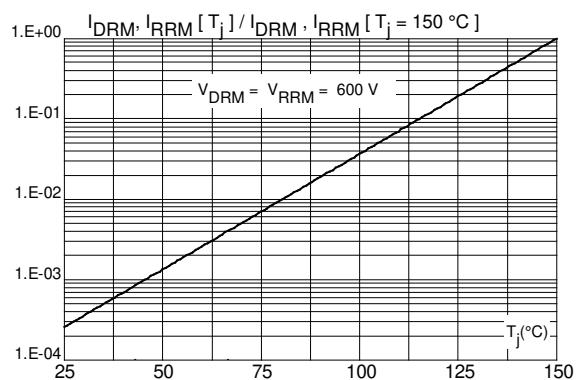
**Figure 9: Non repetitive surge peak on-state current versus sinusoidal pulse width ( $t_p < 10$  ms).**



**Figure 10: On-state characteristics (maximum values)**



**Figure 11: Relative variation of leakage current versus junction temperature ( $t_p < 10$ ms)**



## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
ECOPACK® is an ST trademark.

- Epoxy meets UL 94,V0
- Lead-free package

### 2.1 TO-220AB (NIns. and Ins.) package information

Figure 12: TO-220AB (NIns. & Ins.) package outline

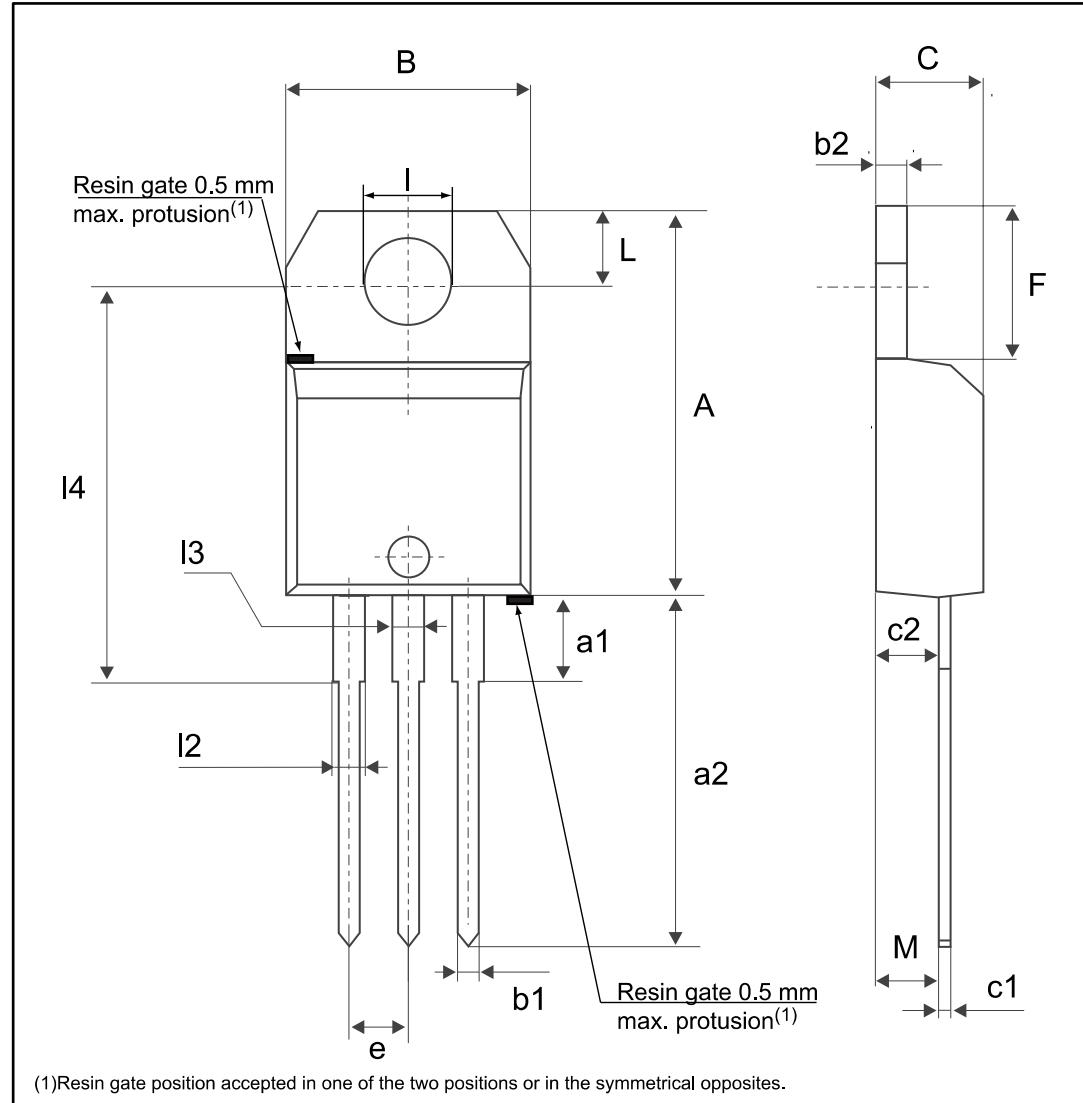


Table 6: TO-220AB (NInch. &amp; In.) package mechanical data

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
B	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
C	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
e	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
I	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
I2	1.14		1.70	0.0449		0.0669
I3	1.14		1.70	0.0449		0.0669
I4	15.80	16.40	16.80	0.6220	0.6457	0.6614
M		2.6			0.1024	

**Notes:**

(1)Inch dimensions are for reference only.

### 3 Ordering information

Figure 13: Ordering information scheme

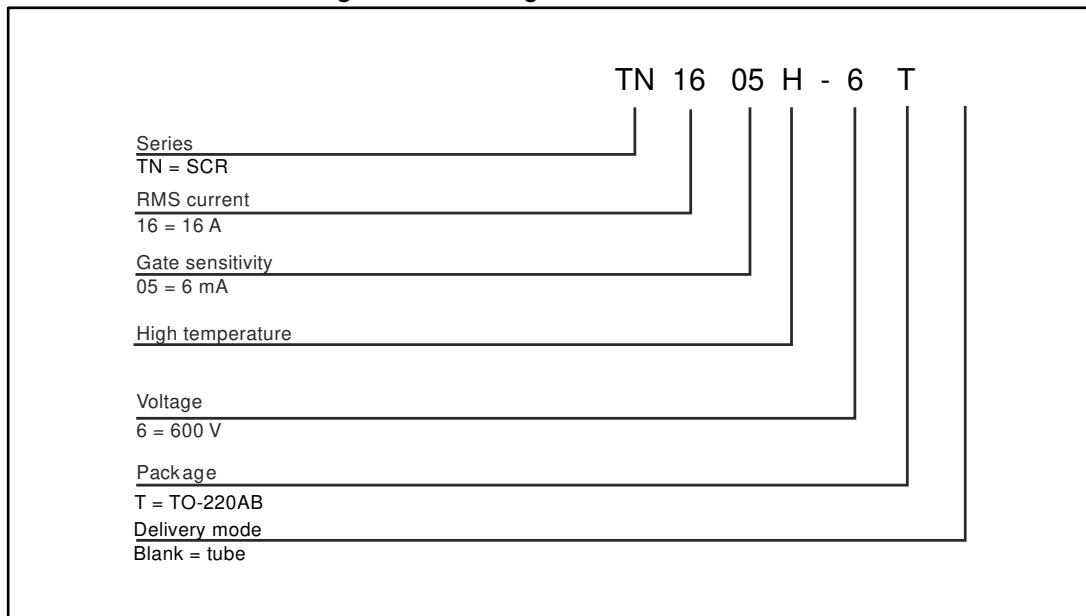


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN1605H-6T	TN1605H6	TO-220AB	2.3 g	50	Tube

### 4 Revision history

Table 8: Document revision history

Date	Revision	Changes
19-May-2017	1	Initial release.

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